

Quantum Coherence Lab Zumbühl Group



Hole Spin Qubit in Ge Hut Wire

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Ge Hole Spin Qubit

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Watzinger et al., Nano Lett. 16, 6879 (2016)

Motivation

- electrically controlled and scalable qubits
- intrinsically strong (and tunable) spin-orbit interaction of holes
 - especially in Germanium/Silicon nanowires
- long spin lifetime and dephasing time (reduced contact hyperfine interaction)
 - due to large HH-LH splitting even longer than in cylindrical nanowires
- study on nature of heavy-hole states in Ge hut wires^[2]
- study on spin states in quantum dots in Ge hut wires^[3]



[1] C. Kloeffel, D. Loss, Annu. Rev. Condens. Matter Phys. 4, 51 (2013)
[2] Watzinger *et al.*, Nano Lett. 16, 6879 (2016)
[3] Li *et al.*, APL 110, 133105 (2017)

Growth

10nm

(a)

- Stranski-Krastanow growth of Ge on Si buffer layer
 - 3-5 nm thick cap of Si to prevent oxidation
- length 1 μ m, triangular cross section
- only [100] and [010] crystal direction



Fig: Theory^[4]





Fig: STEM and AFM images^[2]

[4] Kloeffel *et al.*, arXiv:1712.03476v1

[5] Watzinger *et al.*, APL **2**, 076102 (2014)

[1] Zhang *et al.*, PRL **109**, 085502 (2012)
[2] Watzinger *et al.*, Nano Lett. **16**, 6879
(2016)
[3] Li *et al.*, APL **110**, 133105 (2017)

EDSR spectroscopy



Fig: (a) Bias triangles show Pauli spin blockade

(b) Zero detuning current as function of drive frequency and magnetic field^[1]

Fig: g-factor anisotropy^[1]. φ: angle between [100] and B-field

[1] Watzinger *et al.*, arXiv:1802.00395v2

Coherent Rabi Oscillations



Fig: Rabi oscillations (B = 127 mT, f_{drive} = 5.96555 GHz)^[1]

• initialize in triplet state

- apply microwave burst of duration τ_{burst} in Coulomb blockade
- spin readout in spin blockade region

• Rabi frequency up to 140 MHz

[1] Watzinger *et al.*, arXiv:1802.00395v2

Ramsey

• apply two $\frac{\pi}{2}$ pulses with delay τ_{wait}

• average $T_2^* \approx 130$ ns



Fig: Ramsey fringes (P_{RF} = 11 dBm, B = 127 mT, f_{drive} = 5.96555 GHz)^[1]

[1] Watzinger *et al.*, arXiv:1802.00395v2

Single Shot Readout



- three stage pulsing sequence for spin to charge conversion
- fidelities:
 - spin-down: 0.832 ± 0.005
 - spin-up: 0.923 ± 0.008
 - charge readout: 93 %
- probably limited by T₁
 - 88 ± 5µs at 500 mT
 - 32 ± 2µs at 1100 mT

[1] Vukušić *et al.*, arXiv:1803:01775v2 [2] Vukušić et al., Nano Lett. 17, 5706 (2017)

280

x10⁻⁵

threshold

140

0.4 0.6 0.8 1.0 1.2 Normalized threshold

270

160

120

F. 0.8

260

t (us)

bility

0.4

Coupling to Superconducting Resonator

• hole resonator coupling $\frac{g_c}{2\pi}$ = 148 MHz

• spin-resonator coupling $\frac{g_s}{2\pi}$ = 2-4 MHz



Fig: Resonator with integrated quantum dot devices^[1]

[1] Li et al., Nano Lett. 18, 2091 (2018)

• $\frac{\lambda}{2}$ alumina resonator

• quality factor 810

• 5.972 GHz

• $\frac{\kappa}{2\pi}$ =7.37 MHz

• $\frac{\gamma}{2\pi}$ = 6 MHz

Summary and Outlook

- Ge hut wire: CMOS compatible platform, isotopic purification, strong SOI
- electric dipole spin resonance in double quantum dot
 - Rabi frequency 140 MHz
- Ramsey experiments: $T_2^* \approx 130$ ns
- Single shot readout
- coupling to microwave resonator
- strong spin-resonator coupling?
- long-range coupling and spin entanglement?



Pauli Spin Blockade

